

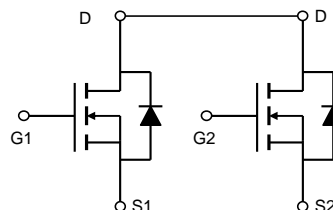
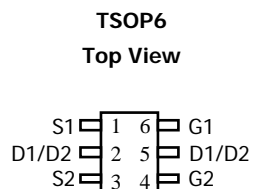
SMC8205AS6-TRG-VB Datasheet

Dual N-Channel MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.024 at $V_{GS} = 4.5$ V	6.0
	0.028 at $V_{GS} = 2.5$ V	5.0

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFETs
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	20		V	
Gate-Source Voltage	V_{GS}	± 12			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	6.0	5.2	A
		$T_A = 70$ °C	4.8	4.2	
Pulsed Drain Current	I_{DM}	30			
Continuous Source Current (Diode Conduction) ^a	I_S	1.5	1.0		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	1.5	1.0	W
		$T_A = 70$ °C	0.96	0.64	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ.	Max.	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	72	83	°C/W
		Steady State	100	120	
Maximum Junction-to-Foot (Drain)	R_{thJF}	55	70		

Notes:

a. Surface Mounted on FR4 board, $t \leq 10$ s.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

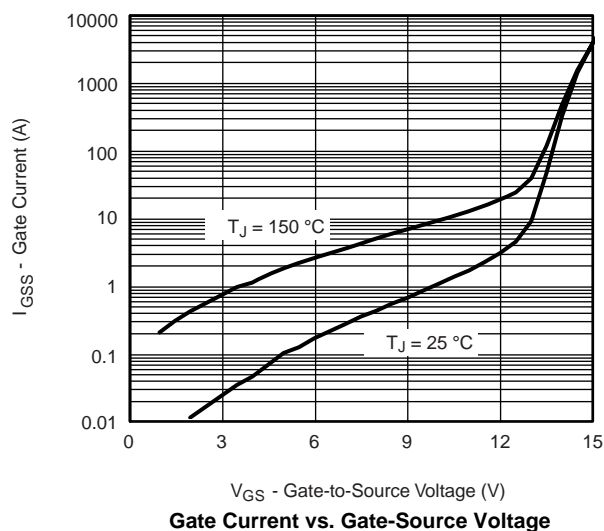
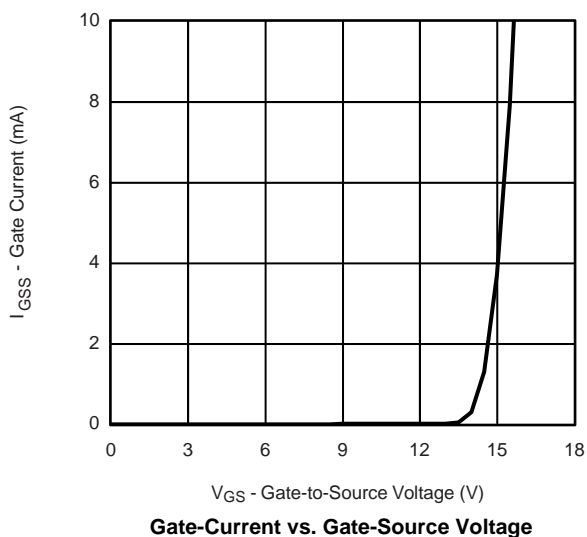
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.5		1.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			± 200	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			25	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = 4.5\text{ V}$	30			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 5.5\text{ A}$		0.024		Ω
		$V_{GS} = 2.5\text{ V}, I_D = 3.5\text{ A}$		0.028		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 5.5\text{ A}$		30		S
Diode Forward Voltage ^b	V_{SD}	$I_S = 1.5\text{ A}, V_{GS} = 0\text{ V}$		0.71	1.2	V
Dynamic^a						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5.5\text{ A}$		12	18	nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			3.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_G = 6\text{ }\Omega$		245	365	ns
Rise Time	t_r			330	495	
Turn-Off Delay Time	$t_{d(off)}$			860	1300	
Fall Time	t_f			510	765	

Notes:

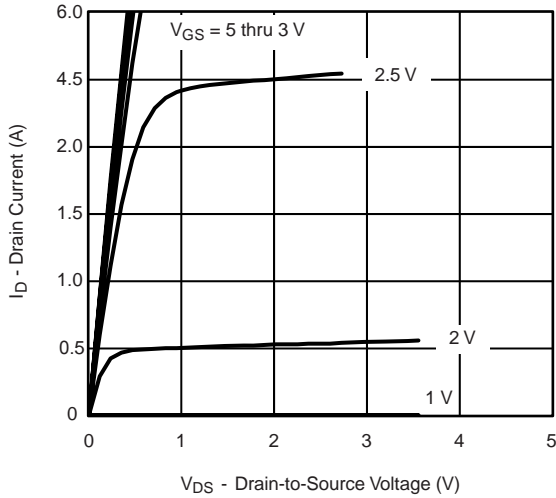
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

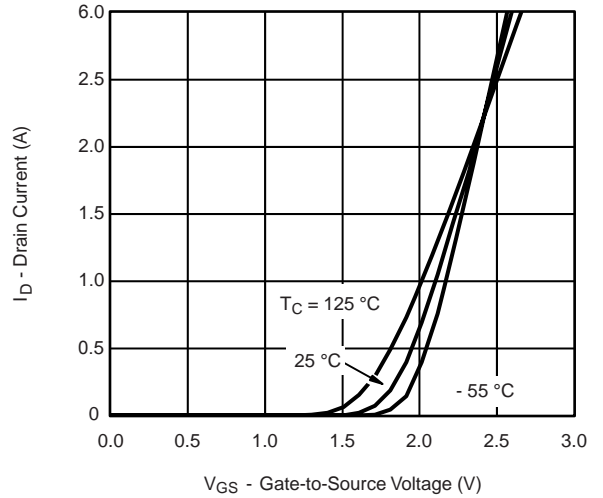
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



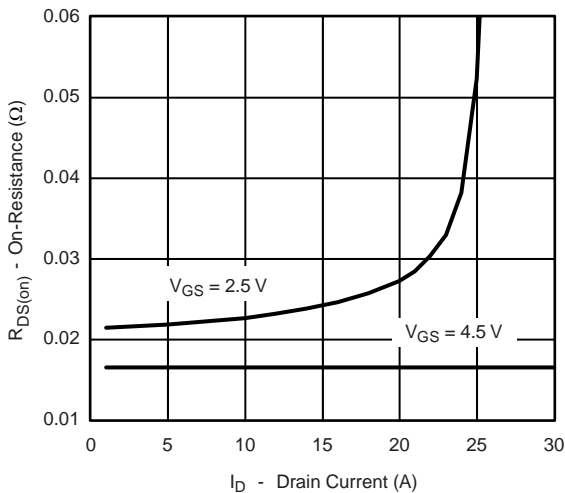
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



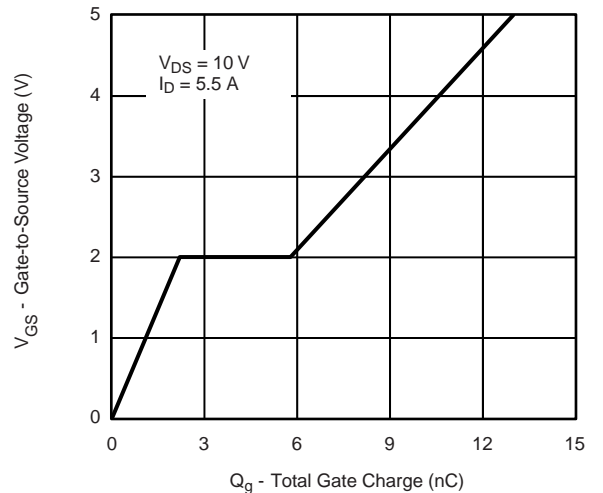
Output Characteristics



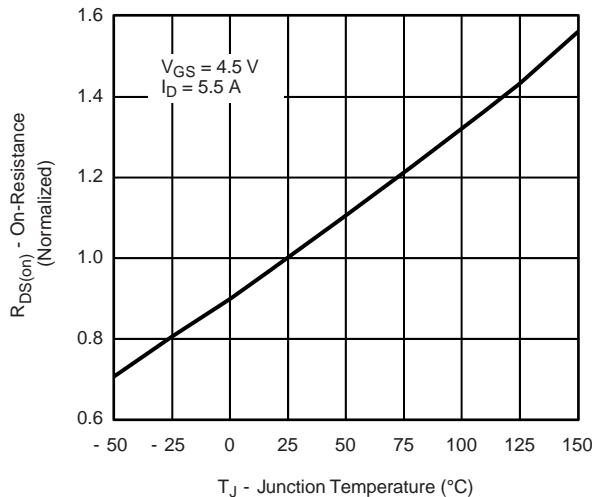
Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

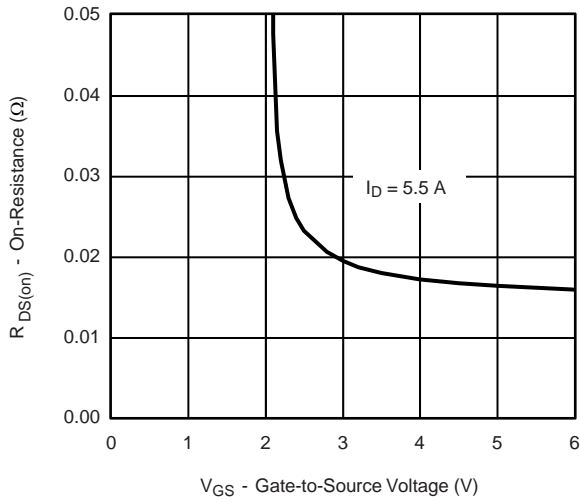


On-Resistance vs. Junction Temperature

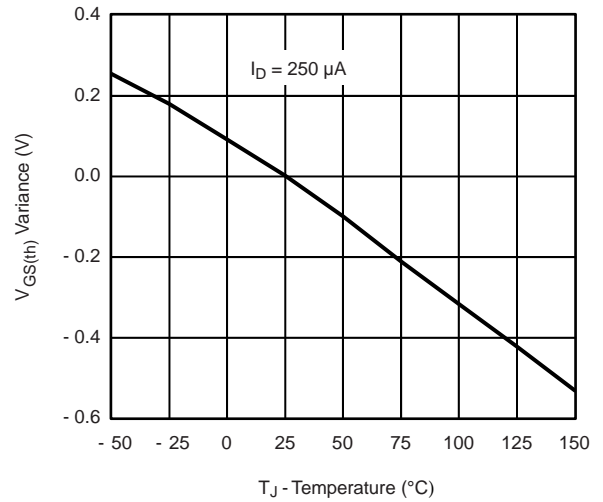


Source-Drain Diode Forward Voltage

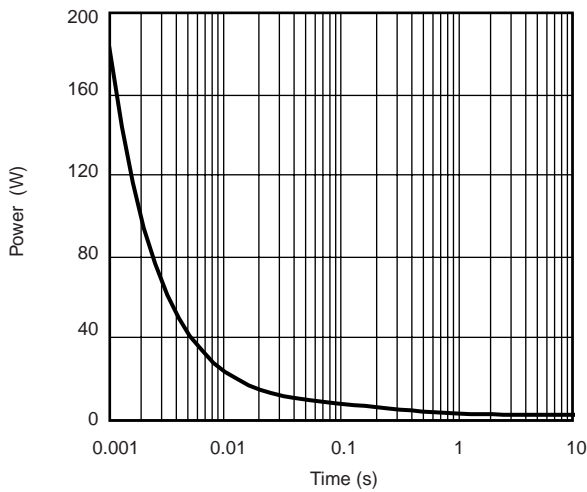
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



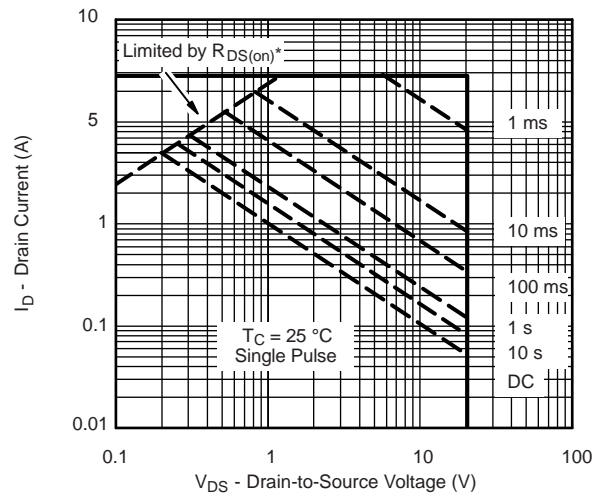
On-Resistance vs. Gate-to-Source Voltage



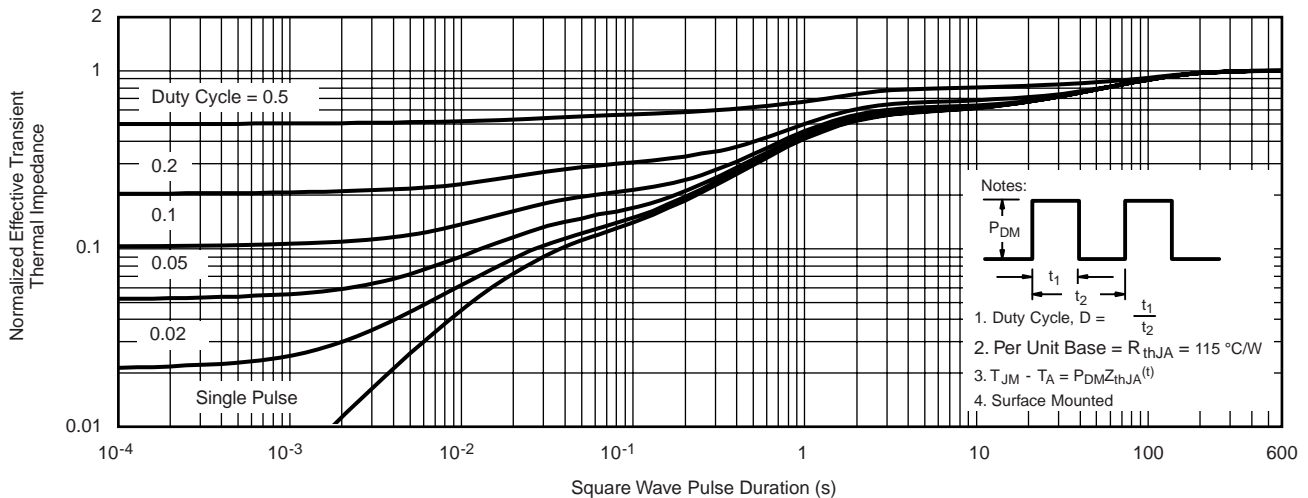
Threshold Voltage



Single Pulse Power



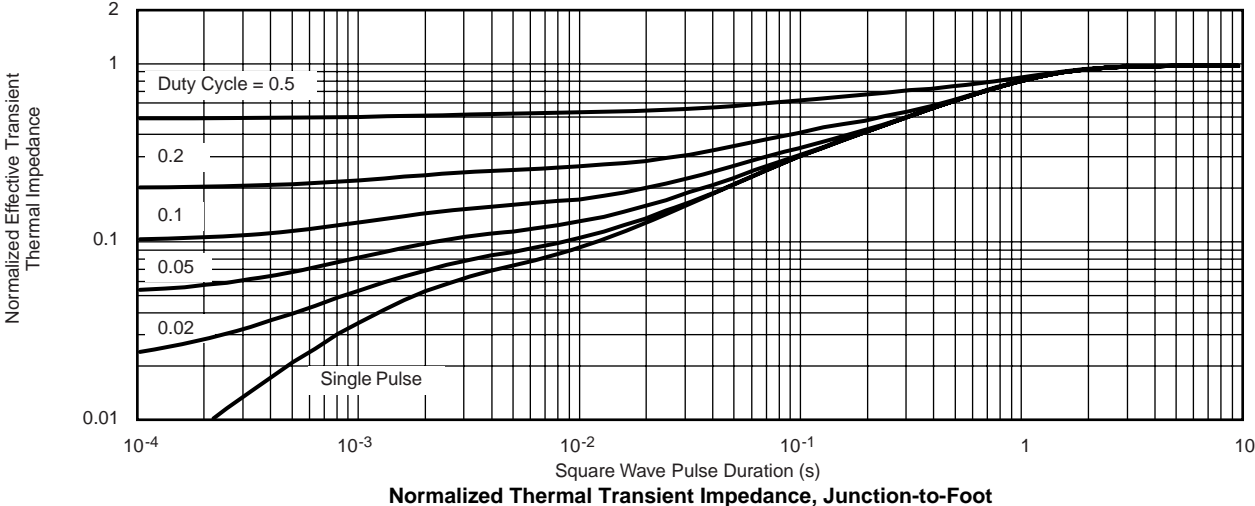
*** V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified
Safe Operating Area, Junction-to-Case**



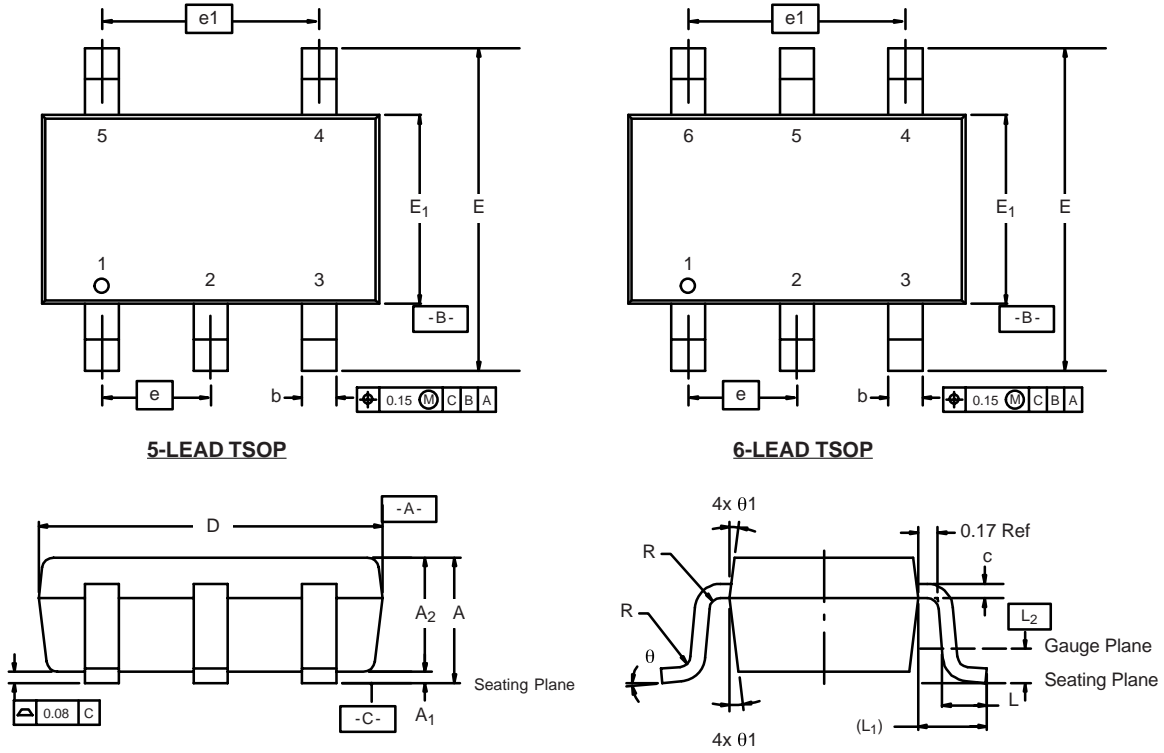
- Notes:
- Duty Cycle, $D = \frac{t_1}{t_2}$
 - Per Unit Base = $R_{thJA} = 115 \text{ } ^\circ\text{C/W}$
 - $T_{JM} - T_A = P_{DM}Z_{thJA}(t)$
 - Surface Mounted

Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

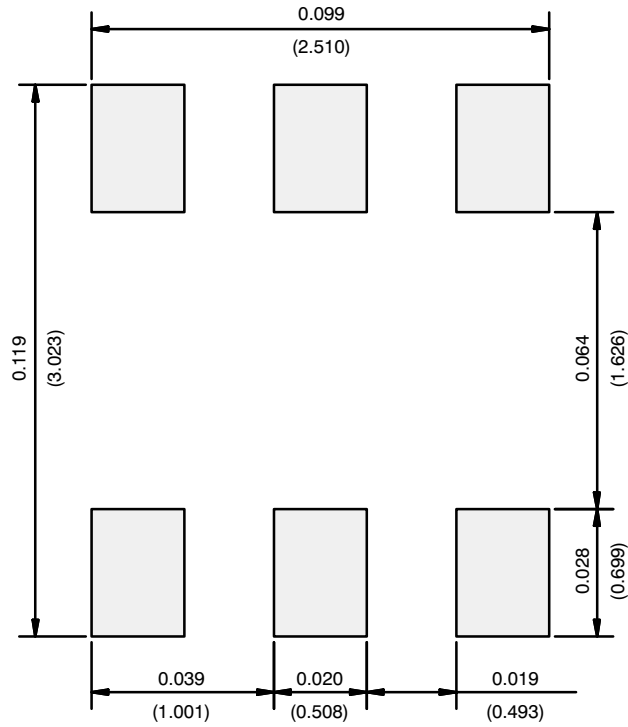


TSOP: 5/6-LEAD
JEDEC Part Number: MO-193C



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads
Dimensions in Inches/(mm)

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